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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f215ret6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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F	Peripherals	STM32F	215Rx	STM32	2F215Vx	STM32	215Zx	STM32F217Vx		STM32F217Zx		STM32F217Ix		
Flash memory in Kb	oytes	512	1024	512	1024	512	1024	512	1024	512	1024	512	1024	
CDAM in Khyton	System			•	•		128	8(112+16)		•			-	
SRAW III Royles	Backup	4		4		4		2	ŀ		4	4		
FSMC memory controller		No	No Yes ⁽¹⁾											
Ethernet ⁽²⁾			No Yes											
	General-purpose							10						
	Advanced-control		2											
Timers	Basic		2											
	IWDG		Yes											
	WWDG	Yes												
RTC								Yes						
Random number generator		Yes												
Communication	SPI / (I ² S)	3/(2) ⁽³⁾												
	l ² C	3												
	USART UART	4 2												
Interfaces	USB OTG FS	Yes												
	USB OTG HS							Yes						
	CAN		2											
Camera interface ⁽²⁾			No									Yes		
Encryption								Yes						
GPIOs		51		8	32	11	4	8	2		114	1	140	
SDIO								Yes						
12-bit ADC								3						
Number of channels	3	16	6		16	2	1	1	6		24		24	
12-bit DAC Number of channels		Yes 2												
Maximum CPU freq	uency						1	20 MHz						
Operating voltage							1.8	V to 3.6 V						

Table 2. STM32F215xx and STM32F217xx: features and peripheral counts

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STM32F21xxx





1. RFU = reserved for future use.





1. RFU = reserved for future use.

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There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode
- LPR is used in Stop modes

The LP regulator mode is configured by software when entering Stop mode.

• Power-down is used in Standby mode.

The Power-down mode is activated only when entering Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost).

Two external ceramic capacitors should be connected on V_{CAP_1} and V_{CAP_2} pin. Refer to *Figure 17: Power supply scheme* and *Table 15: VCAP1/VCAP2 operating conditions*.

All packages have the regulator ON feature.

3.16.2 Regulator OFF

This feature is available only on packages featuring the REGOFF pin. The regulator is disabled by holding REGOFF high. The regulator OFF mode allows to supply externally a V12 voltage source through V_{CAP 1} and V_{CAP 2} pins.

The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to *Figure 17: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V12. An external power supply supervisor should be used to monitor the V12 of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V12 power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset the part of the 1.2 V logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used at power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection at reset or pre-reset is required.

Regulator OFF/internal reset ON

On UFBGA176 package, REGOFF must be connected to V_{DD}.

The regulator OFF/internal reset ON mode allows to supply externally a 1.2 V voltage source through V_{CAP} 1 and V_{CAP} 2 pins, in addition to V_{DD} .



The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the timers TIM1, TIM2, TIM3, TIM4, TIM5 and TIM8 can be internally connected to the ADC start trigger and injection trigger, respectively, to allow the application to synchronize A/D conversion and timers.

3.35 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 12-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

3.36 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.8 and 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

3.37 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.



		Pins	5							
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176	Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
22	31	42	52	P3	PA6	I/O	FT	(4)	SPI1_MISO, TIM8_BKIN, TIM13_CH1, DCMI_PIXCLK, TIM3_CH1, TIM1_BKIN, EVENTOUT	ADC12_IN6
23	32	43	53	R3	PA7	I/O	FT	(4)	SPI1_MOSI, TIM8_CH1N, TIM14_CH1, TIM3_CH2, ETH_MII_RX_DV, TIM1_CH1N, ETH_RMII_CRS_DV, EVENTOUT	ADC12_IN7
24	33	44	54	N5	PC4	I/O	FT	(4)	ETH_RMII_RXD0,/ ETH_MII_RXD0, EVENTOUT	ADC12_IN14
25	34	45	55	P5	PC5	I/O	FT	(4)	ETH_RMII_RXD1, ETH_MII_RXD1, EVENTOUT	ADC12_IN15
26	35	46	56	R5	PB0	I/O	FT	(4)	TIM3_CH3, TIM8_CH2N, OTG_HS_ULPI_D1, ETH_MII_RXD2, TIM1_CH2N, EVENTOUT	ADC12_IN8
27	36	47	57	R4	PB1	I/O	FT	(4)	TIM3_CH4, TIM8_CH3N, OTG_HS_ULPI_D2, ETH_MII_RXD3, TIM1_CH3N, EVENTOUT	ADC12_IN9
28	37	48	58	M6	PB2/BOOT1 (PB2)	I/O	FT	-	EVENTOUT	-
-	-	49	59	R6	PF11	I/O	FT	-	DCMI_D12, EVENTOUT	-
-	-	50	60	P6	PF12	I/O	FT	-	FSMC_A6, EVENTOUT	-
-	-	51	61	M8	V _{SS}	S	-	-	-	-
-	-	52	62	N8	V _{DD}	S	-	-	-	-
-	-	53	63	N6	PF13	I/O	FT	-	FSMC_A7, EVENTOUT	-
-	-	54	64	R7	PF14	I/O	FT	-	FSMC_A8, EVENTOUT	-
	-	55	65	P7	PF15	I/O	FT	-	FSMC_A9, EVENTOUT	-
-	-	56	66	N7	PG0	I/O	FT	-	FSMC_A10, EVENTOUT	-
	-	57	67	M7	PG1	I/O	FT	-	FSMC_A11, EVENTOUT	-
-	38	58	68	R8	PE7	I/O	FT	-	FSMC_D4, TIM1_ETR, EVENTOUT	

Table 7. STM32F21x pin and ball definitions (continued)



•	Table 7. STM32F21	x pin	and	ball	definitions	(continued)

		Pins	\$							
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176	Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
-	-	132	160	B7	PG15	I/O	FT	-	USART6_CTS, DCMI_D13, EVENTOUT	-
55	89	133	161	A10	PB3 (JTDO/TRACESWO)	I/O	FT	-	JTDO/TRACESWO, SPI3_SCK, I2S3_SCK, TIM2_CH2, SPI1_SCK, EVENTOUT	-
56	90	134	162	A9	PB4	I/O	FT	-	NJTRST, SPI3_MISO, TIM3_CH1, SPI1_MISO, EVENTOUT	-
57	91	135	163	A6	PB5	I/O	FT	-	I2C1_SMBA, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT,TIM3_CH2, SPI1_MOSI, SPI3_MOSI, DCMI_D10, I2S3_SD, EVENTOUT	-
58	92	136	164	B6	PB6	I/O	FT	-	I2C1_SCL, TIM4_CH1, CAN2_TX, DCMI_D5,USART1_TX, EVENTOUT	-
59	93	137	165	B5	PB7	I/O	FT	-	I2C1_SDA, FSMC_NL ⁽⁶⁾ , DCMI_VSYNC, USART1_RX, TIM4_CH2, EVENTOUT	-
60	94	138	166	D6	BOOT0	Ι	В	-	-	V _{PP}
61	95	139	167	A5	PB8	I/O	FT	-	TIM4_CH3,SDIO_D4, TIM10_CH1, DCMI_D6, ETH_MII_TXD3, I2C1_SCL, CAN1_RX, EVENTOUT	-
62	96	140	168	B4	PB9	I/O	FT	-	SPI2_NSS, I2S2_WS, TIM4_CH4, TIM11_CH1, SDIO_D5, DCMI_D7, I2C1_SDA, CAN1_TX, EVENTOUT	-
-	97	141	169	A4	PE0	I/O	FT	-	TIM4_ETR, FSMC_NBL0, DCMI_D2, EVENTOUT	-
-	98	142	170	A3	PE1	I/O	FT	-	FSMC_NBL1, DCMI_D3, EVENTOUT	-
-	-	-	-	D5	V _{SS}	S		-	-	-



6.1.6 Power supply scheme



Figure 17. Power supply scheme

 Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

2. To connect REGOFF pin, refer to Section 3.16: Voltage regulator.

3. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.

4. The 4.7 μF ceramic capacitor must be connected to one of the V_{DD} pin.

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.



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6.1.7 Current consumption measurement



Figure 18. Current consumption measurement scheme

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 10: Voltage characteristics*, *Table 11: Current characteristics*, and *Table 12: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Мах	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD}) ⁽¹⁾	-0.3	4.0	
V	Input voltage on five-volt tolerant pin ⁽²⁾	V _{SS} -0.3	V _{DD} +4	V
VIN	Input voltage on any other pin	V _{SS} -0.3	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	m\/
$ V_{SSX} - V_{SS} $	Variations between all the different ground pins	-	50	IIIV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.14: Absolute maximum ratings (electrical sensitivity)		-

Table 10.	Voltage	characteristics
-----------	---------	-----------------

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum value must always be respected. Refer to *Table 11* for the values of the maximum allowed injected current.



Symbol	Ratings	Мах	Unit
I _{VDD}	Total current into V _{DD} power lines (source) ⁽¹⁾	120	
I _{VSS}	Total current out of V_{SS} ground lines (sink) ⁽¹⁾	120	
I _{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	25	mA
. (2)	Injected current on five-volt tolerant I/O ⁽³⁾	-5/+0	
INJ(PIN)	Injected current on any other pin ⁽⁴⁾	±5	
$\Sigma I_{\rm INJ(PIN)}^{(4)}$	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	±25	

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. Negative injection disturbs the analog performance of the device. See note in Section 6.3.20: 12-bit ADC characteristics.

3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN} \le V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 10* for the values of the maximum allowed input voltage.

4. A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS} . $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 10* for the values of the maximum allowed input voltage.

5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	–65 to +150	°C
TJ	Maximum junction temperature	125	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 13. General operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	120	
f _{PCLK1}	Internal APB1 clock frequency	-	0	30	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	60	





Figure 19. Number of wait states versus $f_{\mbox{CPU}}$ and $V_{\mbox{DD}}$ range

6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 15*.



1. Legend: ESR is the equivalent series resistance.

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 µF
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2 μF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

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Figure 32. ACC_{HSI} versus temperature

Low-speed internal (LSI) RC oscillator

Table 32. LSI oscillator characteristics (1)	!
--	---	---	---

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽²⁾	Frequency	17	32	47	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	15	40	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	μA

1. V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Guaranteed by characterization results, not tested in production.

3. Guaranteed by design, not tested in production.



Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105$ °C conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in Table 44.

		Functional susceptibility			
Symbol	Description	Negative injection	Positive injection	Unit	
	Injected current on BOOT0 pin	-0	NA		
I _{INJ}	Injected current on NRST pin	-0	NA	m (
	Injected current on TTa pins: PA4 and PA5	-0	+5		
	Injected current on all FT pins	-5	NA		

Table 44. I/O current injection susceptibility⁽¹⁾

1. NA stands for "not applicable".

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



Symbol	Parameter	Conditions	Min	Max	Unit
t _{res(TIM)}	Timer resolution time	AHB/APB2	1	-	t _{TIMxCLK}
		from 1, f _{TIMxCLK} = 120 MHz	8.3	-	ns
		AHB/APB2	1	-	t _{TIMxCLK}
		f _{TIMxCLK} = 60 MHz	16.7	-	ns
f	Timer external clock		0	f _{TIMxCLK} /2	MHz
'EXT	frequency on CH1 to CH4		0	60	MHz
Res _{TIM}	Timer resolution	(-	16	bit
+	16-bit counter clock period when internal clock is selected	$T_{TIMxCLK} = 120 \text{ MHz}$	1	65536	t _{TIMxCLK}
^I COUNTER		AF 62 - 00 WH 12	0.0083	546	μs
	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
^I MAX_COUNT			-	35.79	S

 Table 50. Characteristics of TIMx connected to the APB2 domain⁽¹⁾

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

6.3.19 Communications interfaces

I²C interface characteristics

STM32F215xx and STM32F217xx I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 51*. Refer also to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).





Figure 45. USB OTG FS timings: definition of data signal rise and fall time

Table 57. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics								
Symbol	Parameter	Conditions	Min	Мах	Unit			
t _r	Rise time ⁽²⁾	C _L = 50 pF	4	20	ns			
t _f	Fall time ⁽²⁾	C _L = 50 pF	4	20	ns			
t _{rfm}	Rise/fall time matching	t _r /t _f	90	110	%			
V _{CRS}	Output signal crossover voltage	-	1.3	2.0	V			

1. Guaranteed by design, not tested in production.

2. Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Table 58 shows the USB HS operating voltage.

Table 58. USB HS DC electrical characteristics

Symb	ol	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level	V _{DD}	USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 59. Clock timing parameters

Parameter ⁽¹⁾		Symbol	Min	Nominal	Max	Unit
Frequency (first transition)	8-bit ±10%	F _{START_8BIT}	54	60	66	MHz
Frequency (steady state) ±500 ppm		F _{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition)	8-bit ±10%	D _{START_8BIT}	40	50	60	%
Duty cycle (steady state) ±500 ppm		D _{STEADY}	49.975	50	50.025	%
Time to reach the steady state frequency and duty cycle after the first transition		T _{STEADY}	-	-	1.4	ms
Clock startup time after the	Peripheral	T _{START_DEV}	-	-	5.6	me
de-assertion of SuspendM	Host	T _{START_HOST}	-	-	-	1115
PHY preparation time after the first transition of the input clock		T _{PREP}	-	-	-	μs

1. Guaranteed by design, not tested in production.



General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 52* or *Figure 53*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.





V_{REF+} and V_{REF} inputs are both available on UFBGA176 package. V_{REF+} is also available on all packages except for LQFP64. When V_{REF+} and V_{REF} are not available, they are internally connected to V_{DDA} and V_{SSA}.





Figure 66. PC Card/CompactFlash controller waveforms for attribute memory write access

1. Only data bits 0...7 are driven (bits 8...15 remains Hi-Z).

Figure 67. PC Card/CompactFlash controller waveforms for I/O space read access







Figure 71. NAND controller waveforms for common memory read access

Figure 72. NAND controller waveforms for common memory write access



Table 81. Switching characteristics for NAND Flash read cycles⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
t _{w(N0E)}	FSMC_NOE low width	4T _{HCLK} - 1	4T _{HCLK} + 2	ns
t _{su(D-NOE)}	FSMC_D[15-0] valid data before FSMC_NOE high	9	-	ns
t _{h(NOE-D})	FSMC_D[15-0] valid data after FSMC_NOE high	3	-	ns
t _{d(ALE-NOE)}	FSMC_ALE valid before FSMC_NOE low	-	3T _{HCLK}	ns
t _{h(NOE-ALE)}	FSMC_NWE high to FSMC_ALE invalid	3T _{HCLK} + 2	-	ns

1. C_L = 30 pF.

2. Guaranteed by characterization results, not tested in production.



Device marking

Figure 79 gives an example of topside marking orientation versus Pin 1 identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



7.5 UFBGA176+25 package information



Figure 85. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline

1. Drawing is not to scale.

Table 90. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters		inches ⁽¹⁾			
	Min	Тур	Мах	Min	Тур	Мах
A	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	9.100	-	-	0.3583	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	9.100	-	-	0.3583	-
е	-	0.650	-	-	0.0256	-
Z	-	0.450	-	-	0.0177	-
ddd	-	-	0.080	-	-	0.0031

